



BUK652R1-30C,127 Information

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For Reference Only

Part Number BUK652R1-30C,127

Manufacturer NXP

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 120A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BUK652R1-30C,127 Specifications

Manufacturer Part Number BUK652R1-30C,127 Manufacturer NXP Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.8V @ ImA Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 263W (Tc) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) #16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB To-220AB	Manufacturer Part Number	BUK652R1-30C,127
Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.8V @ 1mA Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 263W (Tc) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	NXP
Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.8V @ 1mA Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 263W (Tc) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Category	Discrete Semiconductor Products
Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.8V @ 1mA Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 263W (Tc) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.8V @ 1mA Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 263W (Tc) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V 20V 30V 20A (Tc) 120A (Tc) 120A (Tc) 120A (Tc) 120A (Tc) 128Y @ 1mA 12918pF @ 25V 12918	Series	TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Poperating Type Through Hole Supplier Device Package Package / Case 30V 120A (Tc) 128V @ ImA 168nC @ 10V 10918pF @ 25V 169V 169V 169V 169V 169V 169V 169V 169V 170V 170	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Cate Charge (Qg) (Max) @ Vds 2.8V @ 1mA 168nC @ 10V 10918pF @ 25V 16V 25V 25V 263W (Tc) 24 mOhm @ 25A, 10V Operating Temperature Correct Through Hole Supplier Device Package Package / Case TO-220AB TO-220AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Capacitage Temperature Poperating Temperature Capacitage (Ciss) (Max) Through Hole Supplier Device Package Package / Case 4.5V, 10V 2.8V @ 1mA 168nC @ 10V 10918pF @ 25V 25V 263W (Tc) 263W (Tc) 2.4 mOhm @ 25A, 10V Through Hole TO-220AB TO-220AB	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id 2.8V @ 1mA Gate Charge (Qg) (Max) @ Vgs 168nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 263W (Tc) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	120A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jenus Andrew	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 10918pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	2.8V @ 1mA
Vgs (Max) $\pm 16V$ FET Feature-Power Dissipation (Max) $263W$ (Tc)Rds On (Max) @ Id, Vgs 2.4 mOhm @ $25A$, $10V$ Operating Temperature -55° C ~ 175° C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	168nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	10918pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.4 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs2.4 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	263W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	2.4 mOhm @ 25A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

BUK652R1-30C,127 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BUK652R1-30C,127 Payment Methods



















BUK652R1-30C,127 Shipping Methods













If you have any question about BUK652R1-30C,127, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com